

FDMC2674

N-Channel UltraFET Trench® MOSFET

220V, 1A, 366mΩ

Features

- Max $r_{DS(on)}$ = 366mΩ at $V_{GS} = 10V$, $I_D = 1A$
- Typ Q_g = 12.7nC at $V_{GS} = 10V$
- Low Miller charge
- Low Q_{rr} Body Diode
- Optimized efficiency at high frequencies
- UIS Capability (Single Pulse and Repetitive Pulse)
- RoHS Compliant

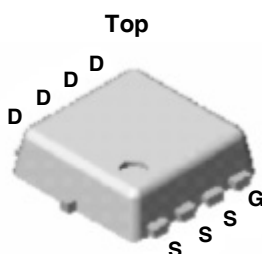
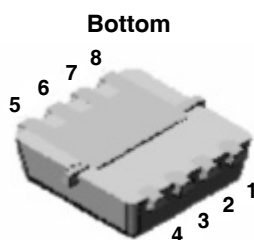


General Description

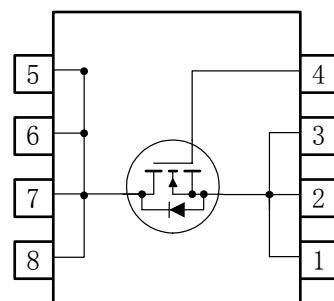
UltraFET® device combines characteristics that enable benchmark efficiency in power conversion applications. Optimized for $r_{DS(on)}$, low ESR, low total and Miller gate charge, these devices are ideal for high frequency DC to DC converters.

Applications

- DC/DC converters and Off-Line UPS
- Distributed Power Architectures



MLP 3.3x3.3



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	220	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous	1	A
	-Pulsed	13.8	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	13	mJ
P_D	Power Dissipation for Single Operation	2.4	W
T_J, T_{STG}	Operating and Storage Temperature	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance , Junction to Ambient (Note 1a)	52	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance , Junction to Ambient (Note 1b)	108	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC2674	FDMC2674	MLP 3.3 x 3.3	7"	12mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	220			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		248		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 176\text{V}$, $V_{GS} = 0\text{V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$,			± 100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2	3.4	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		-10.2		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 1\text{A}$		305	366	m Ω
		$V_{GS} = 10\text{V}$, $I_D = 1\text{A}$, $T_J = 150^\circ\text{C}$		678	814	

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 100\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		880	1180	pF
C_{oss}	Output Capacitance			70	95	pF
C_{rss}	Reverse Transfer Capacitance			11	20	pF

Switching Characteristics (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{V}$, $I_D = 1\text{A}$ $V_{GS} = 10\text{V}$, $R_{GS} = 2.4\Omega$		9	18	ns
t_r	Rise Time			13	23	ns
$t_{d(off)}$	Turn-Off Delay Time			15	27	ns
t_f	Fall Time			21	34	ns
Q_g	Total Gate Charge at 10V	$V_{DD} = 15\text{V}$, $V_{GS} = 10\text{V}$, $I_D = 1\text{A}$, $I_G = 1.0\text{mA}$		12.7	18	nC
Q_{gs}	Gate to Source Gate Charge			3.8		nC
Q_{gd}	Gate to Drain Charge			2.9		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = 1\text{A}$		0.8	1.5	V
t_{rr}	Reverse Recovery Time	$I_F = 1\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$			60	ns
Q_{rr}	Reverse Recovery Charge	$I_F = 1\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$			109	nC

Notes:

1: $R_{\theta JA}$ is determined with the device mounted on a 1in² oz.copper pad on a 1.5x1.5 in board of FR-4 material . $R_{\theta JC}$ are guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



a. $52^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b. $108^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%.

3: Starting $T_J = 25^\circ\text{C}$, $L = 3\text{mH}$, $I_{AS} = 3\text{A}$, $V_{DD} = 50\text{V}$, $V_{GS} = 10\text{V}$.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

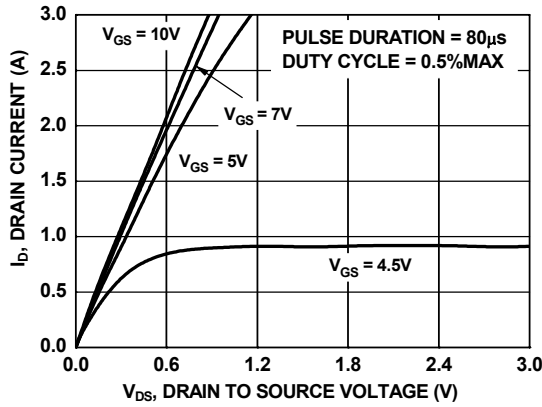


Figure 1. On Region Characteristics

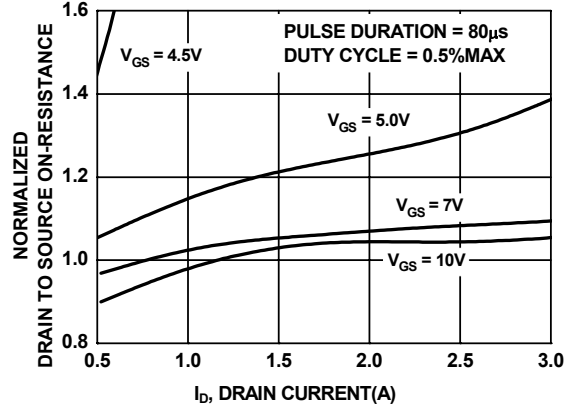


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

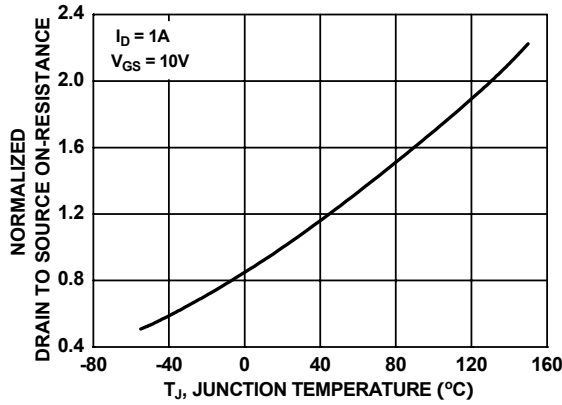


Figure 3. Normalized On Resistance vs Junction Temperature

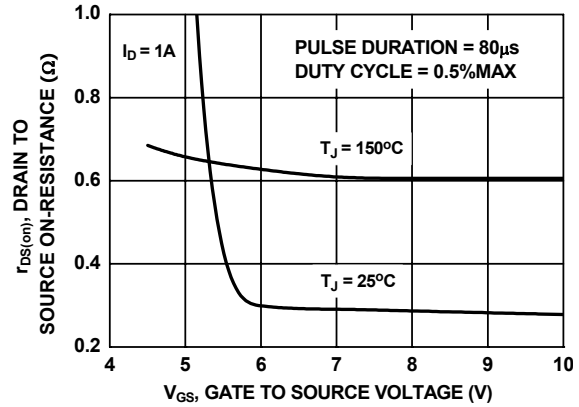


Figure 4. On-Resistance vs Gate to Source Voltage

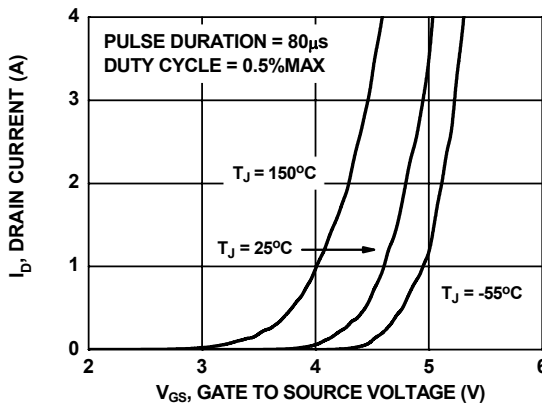


Figure 5. Transfer Characteristics

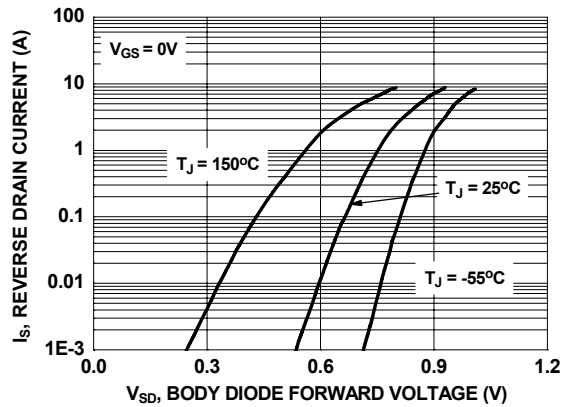


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

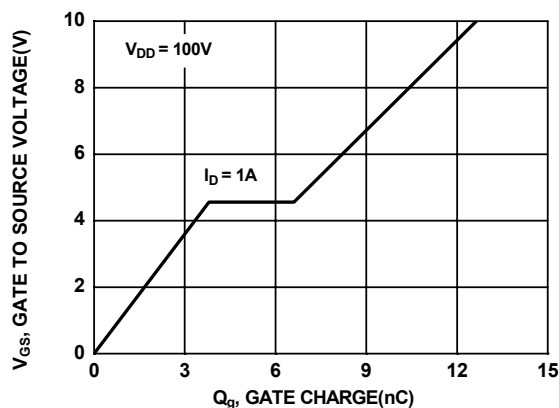


Figure 7. Gate Charge Characteristics

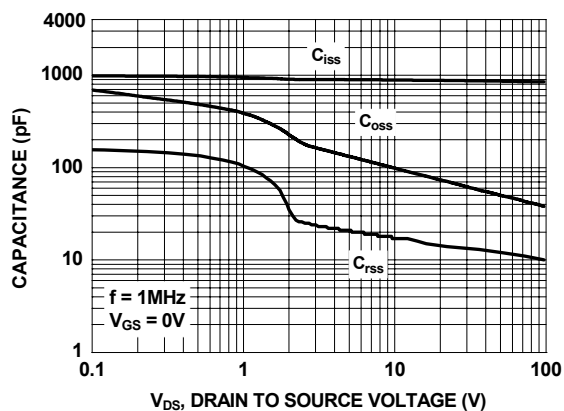


Figure 8. Capacitance vs Drain to Source Voltage

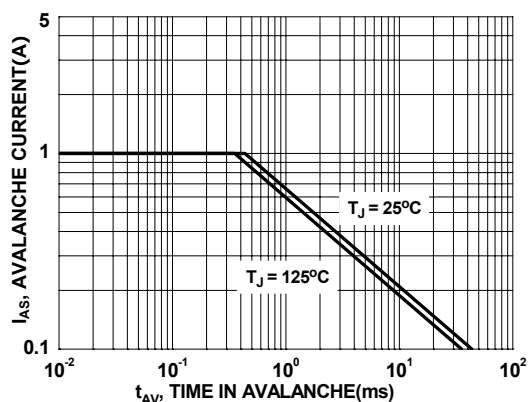


Figure 9. Unclamped Inductive Switching Capability

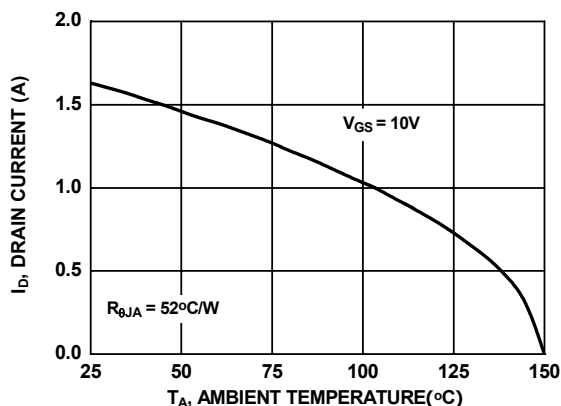


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

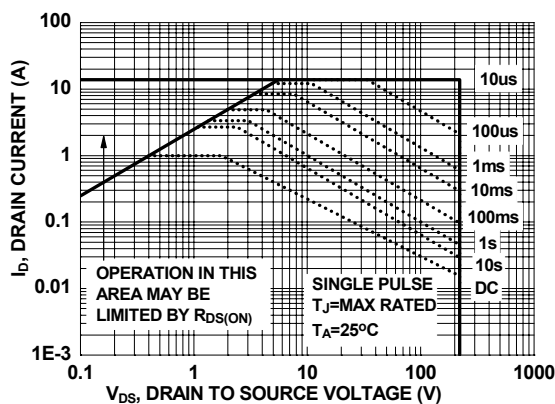


Figure 11. Forward Bias Safe Operating Area

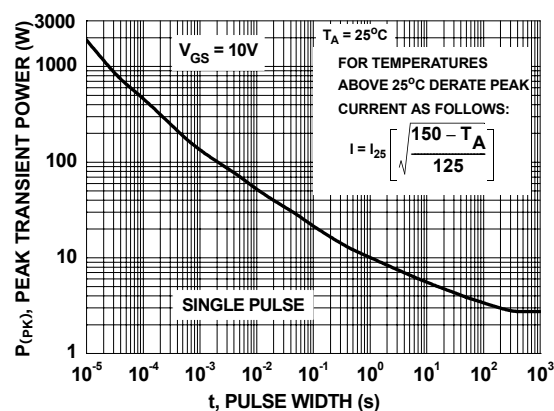
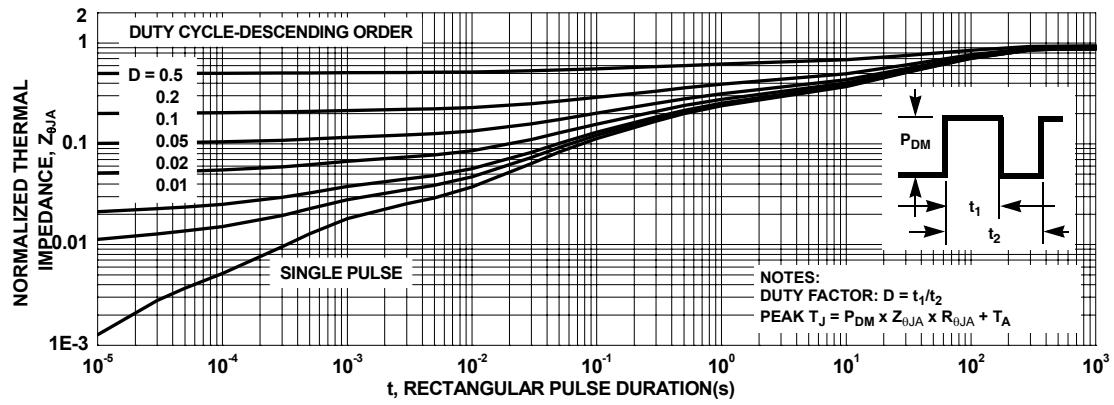


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted



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EnSigna™	ImpliedDisconnect™	OCXPro™	ScalarPump™	VCX™
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